芯 洲 科 技
Silicon Content Technology

PRODUCT RELIABILITY REPORT

Product: SCT2450CSTER

Package & Reliability Department
Silicon Content Technology

3. Failure Rate Calculation

Sample Size:	2278
Rejects:	0
Activation Energy (eV):	0.7
Failure Rate (FIT@60%CL):	1.66 FIT
MTBF (years):	68681 Years

Revision / Update History

Revision	Reason for Change	Date	EQD Engineer
0.0	Initial release	Jul.2022	Joker Bai
1.0	Update HAST	May.2023	Joker Bai
2.0	Update HTOL	May.2024	Joker bai

Appendix: Description of Reliability Test and Failure Rate Calculation

High Temperature Operating Life Test

Purpose: This test is a worst-case life test that checks the integrity of the product. The high temperature testing is use for acceleration of any potential failures over time. The calculation for failure rate (FIT) using the operating ambient temperature is done using the Arrhenius equation.

Condition: 125°C @ V_{in} max

Pass Criteria: All units must pass the min/max limits of the datasheet.

ESD Test

Purpose: The purpose of the ESD test is to guarantee that the device can withstand electrostatic voltages during handling.

Condition: Human Body Model and Charged Device Model

Pass Criteria: ESD testing on every pin. The device must be fully functional after testing and pass the min/max limits in the datasheet.

IC Latch-Up Test

Purpose: The purpose of this specification is to establish a method for determining IC latch-up characteristics and to define latch-up failure criteria. Latch-up characteristics are extremely important in determining product reliability and minimizing No Trouble Found (NTF) and Electrical Overstress (EOS) failures due to latch-up.

Condition: Voltage and current injection

Pass criteria: All pins with the exception of "no connect" pins and timing related pins, shall be latch-up tested. The device must be fully functional after testing and pass the min/max limits in the datasheet.

Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices

Purpose: The purpose of this standard is to identify the classification level of nonhermetic solid state surface mount devices (SMDs) that are sensitive to moisture-induced stress so that they can be properly packaged, stored, and handled to avoid damage during assembly solder reflow attachment and/or repair operations.

Condition: Bake + moisture soak + 3X reflow at 260°C (MSL1: 85 /85%RH/168hours; MSL2: 85 /60%RH/168hours; MSL2a: 30 /60%RH/696hours; MSL3: 30 /60%RH/192hours; MSL4: 30 /60%RH/96hours; MSL5: 30 /60%RH/72hours; MSL5a: 30 /60%RH/48hours; MSL6: 30 /60%RH/TOL;

Pass criteria: All units must pass the min/max limits of the datasheet

High Temperature Storage Life

Purpose: The test is typically used to determine the effects of time and temperature, under storage conditions, for thermally activated failure mechanisms and time-to-failure distributions of solid state electronic devices, including nonvolatile memory devices (data retention failure mechanisms).

Condition: Bake at 150°C

Pass Criteria: All units must pass min/max limits of the datasheet

Accelerated Moisture Resistance- Unbiased Autoclave

Purpose: To check the performance of the device in humid environments. This test checks the integrity of the passivation, poor metal to plastic seal and contamination level during assembly and material compatibility.

Condition: 121°C/15psig/100% RH (no bias)

Pass Criteria: All units must pass min/max limits of the datasheet

Temperature Cycle Test

Purpose: This test is used to evaluate the die attach integrity and bond integrity. This is similar to the Thermal Shock test, but can generate different failure modes due to the longer dwell time and gradual temperature change.

Condition: -65°C to 150°C

Pass Criteria: All units must pass min/max limits of the datasheet

Failure Rate Calculation

The failure rate is gauged by a Failures-In-Time (FIT) based upon accelerated stress data. The unit for FIT is failure per billion device hour.

Where

2 (Chi-Squared) is the goodness-of-fit test statistic at a specified level of confidence;
EDH= Equivalent Device Hours = AF × (Life test sample size) × (test duration);
AF= Acceleration Factor.

High Temperature Operating Life (HTOL) test is usually done under acceleration of temperature and voltage. The total number of failures from the stress test determines the chi-squared factor.

$$AF = AF_T \times AF_V$$

The Temperature Acceleration Factor AF_T:

$$AF_T \quad \exp \frac{E_a}{k} \frac{1}{T_{J\ use}} \quad \frac{1}{T_{J\ stress}}$$

T_{Juse} = Junction temp under typical operating conditions;
$T_{Jstress}$ =Junction temp under accelerated test conditions;
Ea is Activation energy=0.7eV;
K=Boltzmann’s constant=8.62×10^{-5} eV/K.

The voltage Acceleration Factor AF_V:

V_{use} = Gate voltage under typical operating conditions;
V_{stress} = Gate voltage under accelerated test conditions;
= Voltage acceleration factor (in 1/Volts) and specified by technology.

MTBF (Mean Time Between Failure) equals to /FIT (in hours).